



JCT812TC 12A SCR

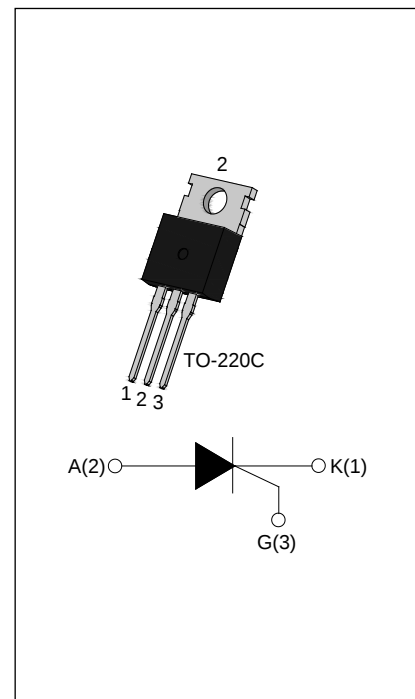
Rev.A.1.1

DESCRIPTION:

JCT812TC silicon controlled rectifier is specifically designed for medium power switching and phase control applications. High current density due to mesa technology; SIPOS and Glass Passivation technology used has reliable operation up to 125°C junction temperature. Low I_{GT} parts available. Package TO-220C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	≤ 5	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
Average on-state current ($T_c \leq 105^\circ\text{C}$)	$I_{T(AV)}$	7.6	A
RMS on-state current ($T_c \leq 105^\circ\text{C}$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	140	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}$, $T_j=25^\circ\text{C}$)		154	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	98	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125^{\circ}\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	-	-	5	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C } R_L=3.3\text{k}\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	30	mA
I_H	$I_T=500\text{mA}$	-	-	15	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$	200	-	-	V/ μs
t_{on}	$I_G=20\text{mA } I_A=200\text{mA } I_R=20\text{mA}$ $T_j=25^{\circ}\text{C}$	-	5	-	μs
t_{off}		-	80	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=24\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.8	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	27	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.25	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	1.3	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient (DC)	55	$^{\circ}\text{C/W}$

ORDERING INFORMATION

J	CT	8	12	T	C
JieJie Microelectronics Co., Ltd.	SCRs				C:TO-220C
	8: $V_{DRM}/V_{RRM} \geq 800V$		12: $I_{T(RMS)}: 12A$	T: $I_{GT} \leq 5mA$	

MARKING

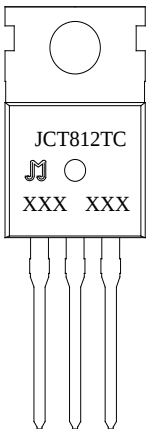
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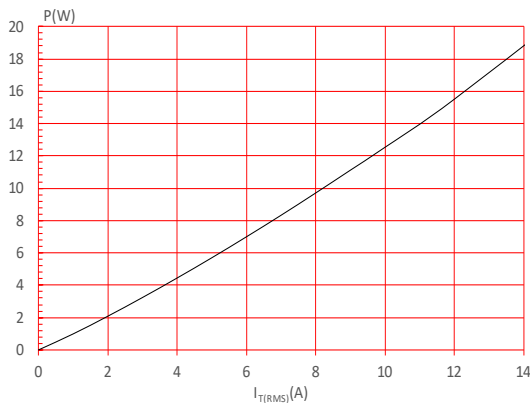
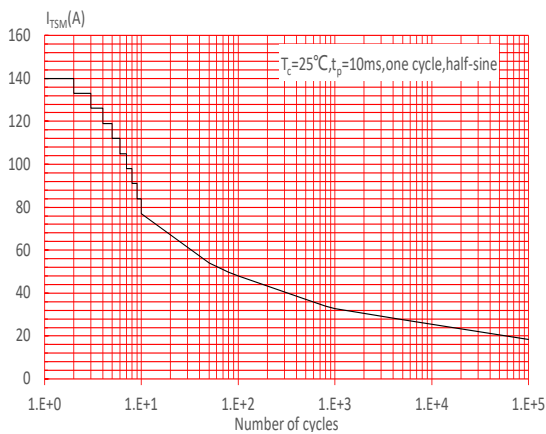
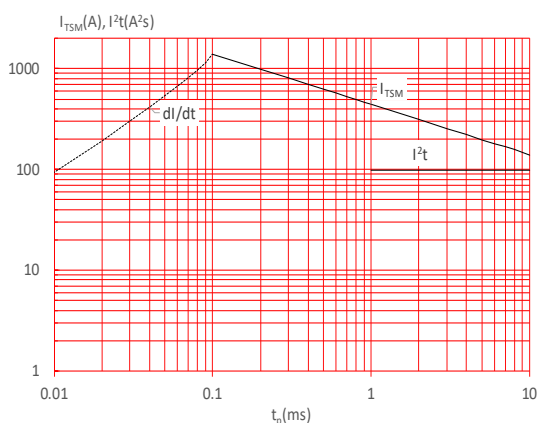
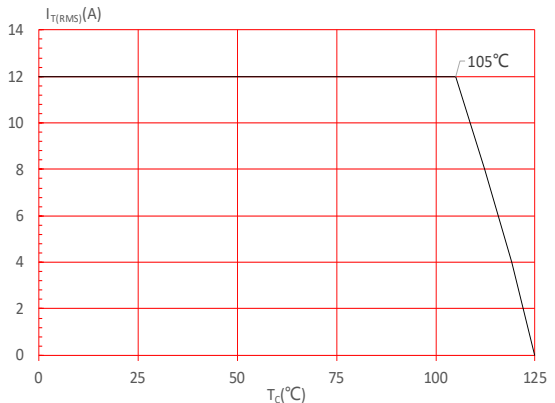
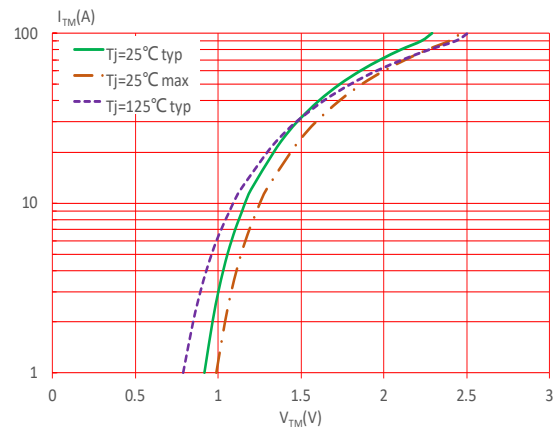
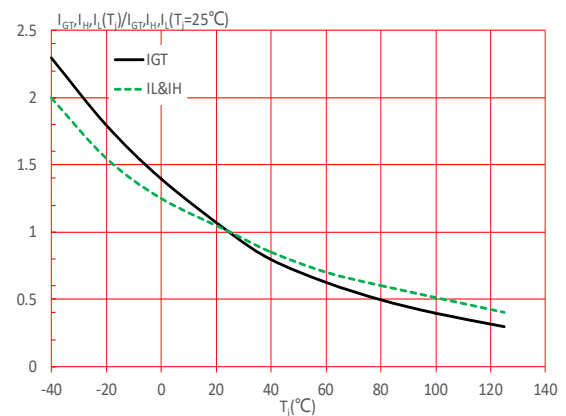
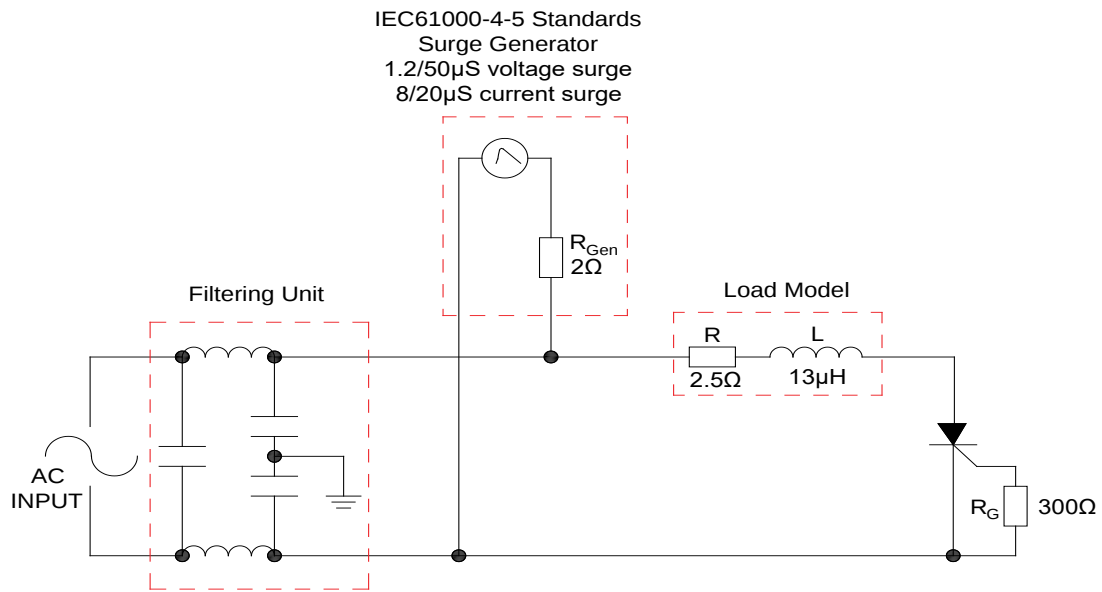
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

FIG.2: RMS on-state current versus case temperature

FIG.4: On-state characteristics

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie Microelectronics

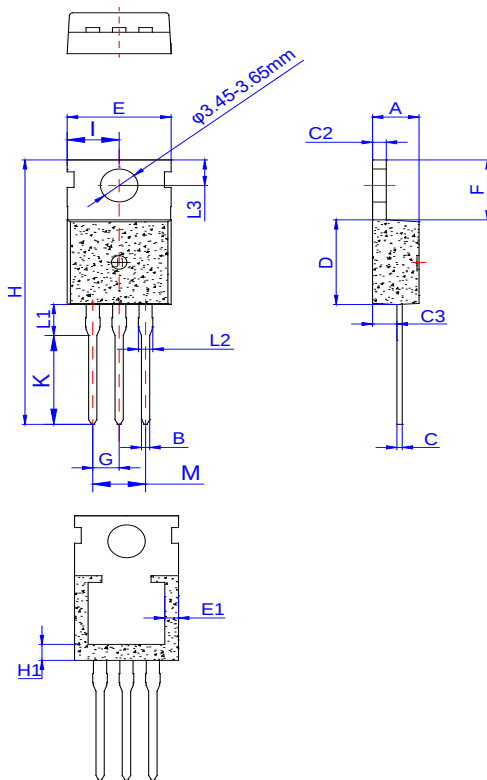
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT812TC	800	5	TO-220C	50	Tube

Document Revision History

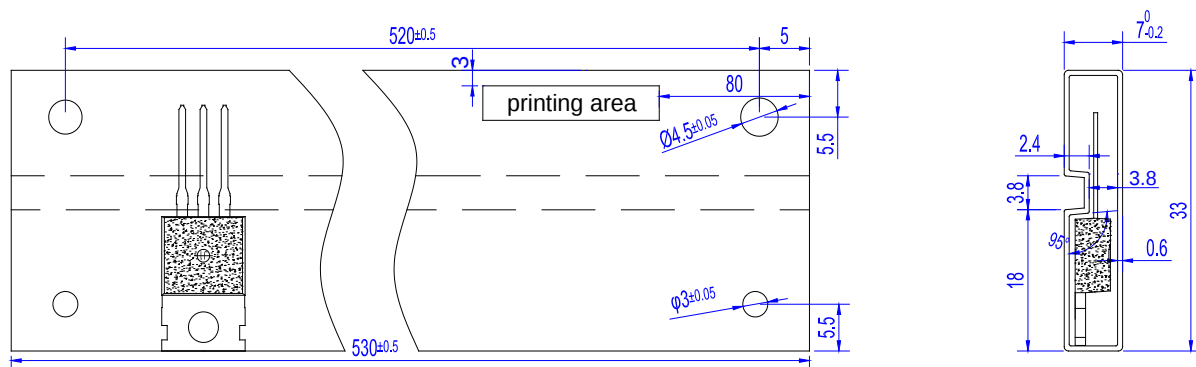
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.14, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.30	0.390		0.406
E1	0.80		1.20	0.031		0.047
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.00		29.80	1.102		1.173
H1	2.15		2.55	0.085		0.100
I	4.70		5.10	0.185		0.201
K	9.90		10.30	0.390		0.406
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
M	4.80		5.20	0.189		0.205

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220C	TUBE	50	1,000	5,000

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